

In the Specification:

Page 6, paragraph 3:

Lastly, it is an object of the present invention [is] to combine all of these unique design aspects and individual fabrication techniques into effective and manufacturable heat dissipating SOI structures.

Page 11, paragraph 2:

Within FIG. 6c (a sectional view of FIG. 6b on lines 6c-6c) the heat absorbing junction [48] 46 (electrically bonding both the substrate 16 and semiconductor 49) is positioned near the center of the substrate 16 (center of the SOI structure 10) and the heat rejecting junction 48 (representing the heat rejecting junctions on the substrate 16 and semiconductor 49) is positioned near the perimeter of the substrate 16 and SOI structure 10.